Product data sheet

1 General description

The BGU8053 is, also known as the BTS1001H, a low noise high linearity amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 2 GHz and 6 GHz. It is housed in a 2 mm × 2 mm × 0.75 mm 8-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

2 Features and benefits

- Low noise performance: NF = 0.56 dB
- High linearity performance: IP3_O = 36 dBm
- High input return loss > 12 dB
- High output return loss > 20 dB
- Unconditionally stable up to 20 GHz
- Programmable bias current (via resistor)
- Small 8-terminal leadless package 2 mm × 2 mm × 0.75 mm
- ESD protection on all terminals
- · Moisture sensitivity level 1
- Fast shut down to support TDD systems
- 3 V to 5 V single supply

3 Applications

- · Wireless infrastructure
- · Low noise and high linearity applications
- LTE, W-CDMA, CDMA, GSM
- · General-purpose wireless applications
- TDD or FDD systems
- · Suitable for small cells



Low noise high linearity amplifier

4 Quick reference data

Table 1. Quick reference data

f = 2500 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; $R\sim$ bias = 5.1 $k\Omega$; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 16 with components listed in Table 9 optimized for f = 2500 MHz.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|---------------------------------------|--|-----|-------|------|------|
| I _{CC} | supply current | on state | 36 | 48 | 60 | mA |
| | | off state | - | 2.8 | - | mA |
| G _{ass} | associated gain | on state | 17 | 18.5 | 20 | dB |
| | | off state | - | -23.5 | - | dB |
| NF | noise figure | [1] | - | 0.56 | 0.75 | dB |
| P _{L(1dB)} | output power at 1 dB gain compression | | - | 18 | - | dBm |
| IP3 _O | output third-order intercept point | 2-tone; tone spacing = 1 MHz;P _i = -15 dBm per tone | 32 | 36 | - | dBm |

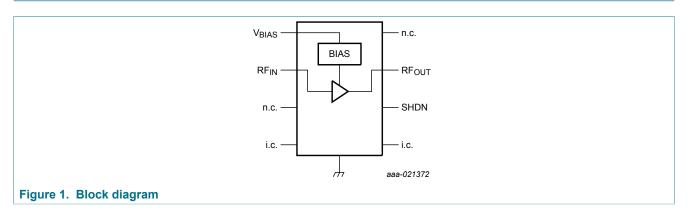
^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

5 Ordering information

Table 2. Ordering information

| Type number | Package | | |
|-------------|---------|--|-----------|
| | Name | Description | Version |
| BGU8053 | HWSON8 | plastic thermal enhanced very very thin small outline package; no leads; 8 terminals; body 2 × 2 × 0.75 mm | SOT1327-1 |

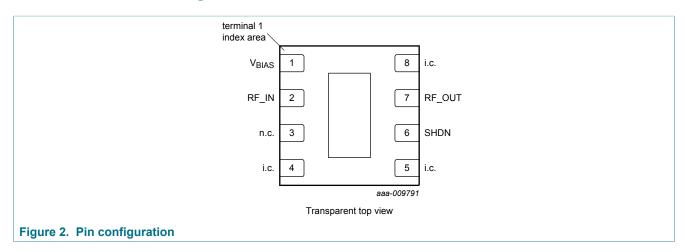
6 Block diagram



Low noise high linearity amplifier

7 Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

| Symbol | Pin | Description |
|------------|-----------------|---|
| V_{BIAS} | 1 | bias voltage |
| RF_IN | 2 | RF input |
| n.c. | 3 | not connected |
| i.c. | 4, 5, 8 | internally connected. Can be grounded or left open in the application |
| SHDN | 6 | shutdown |
| RF_OUT | 7 | RF output |
| GND | exposed die pad | ground |

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Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|-----------------------|------------------------------------|--|-----|-----|------|------|
| V _{CC} | supply voltage | | | - | 6 | V |
| V _{ctrl(sd)} | shutdown control voltage | | | - | 3 | V |
| I _{CC} | supply current | | | - | 85 | mA |
| P _{i(RF)CW} | continuous waveform RF input power | | | - | 20 | dBm |
| T _{stg} | storage temperature | | | -40 | +150 | °C |
| T _j | junction temperature | | | - | 150 | °C |
| Р | power dissipation | T _{case} ≤ 125 °C | [1] | - | 510 | mW |
| V_{ESD} | electrostatic discharge voltage | Human Body Model (HBM) According to ANSI/ESDA/JEDEC standard JS-001-2010 | | - | 1.5 | kV |
| | | Charged Device Model (CDM); According to JEDEC standard 22-C101B | | - | 2 | kV |

Case is ground solder pad.

Recommended operating conditions

Table 5. Recommended operating conditions

| rubic of Recommended operating conditions | | | | | | | |
|---|--------------------------|------------|-----|-----|------|------|--|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit | |
| V _{CC} | supply voltage | | 3.3 | 5 | 5.25 | V | |
| Z_0 | characteristic impedance | | - | 50 | - | Ω | |
| T _{case} | case temperature | | -40 | - | +85 | °C | |

10 Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Тур | Unit |
|-------------------------|--|------------|-----|------|
| $R_{\text{th(j-case)}}$ | thermal resistance from junction to case | [1] [2] | 50 | K/W |

Case is ground solder pad.

Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

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11 Characteristics

Table 7. Characteristics

f = 2500 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; R_{bias} = 5.1 $k\Omega$; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 16 with components listed in Table 9 optimized for f = 2500 MHz

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------------|--|--|-----|-----|-------|------|------|
| I _{CC} | supply current | on state | | 36 | 48 | 60 | mA |
| | | off state | | - | 2.8 | - | mA |
| G _{ass} | associated gain | on state | | 17 | 18.5 | 20 | dB |
| | | off state | | - | -23.5 | - | dB |
| NF | noise figure | | [1] | - | 0.56 | 0.75 | dB |
| P _{L(1dB)} | output power at 1 dB gain compression | | | - | 18 | - | dBm |
| IP3 _O | output third-order intercept point | 2-tone; tone spacing = 1 MHz;P _i = -15 dBm per tone | | 32 | 36 | - | dBm |
| | | 2-tone; tone spacing = 1 MHz;P _i = -15 dBm per tone | [2] | 30 | 34 | - | dBm |
| RLin | input return loss | on state | | - | 12.2 | - | dB |
| | | off state | | - | 6.3 | - | dB |
| RLout | output return loss | | | - | 28.0 | - | dB |
| ISL | isolation | | | - | 22.0 | - | dB |
| t _{s(pon)} | power-on settling time | P_i = -20 dBm; SHDN (pin 6) from HIGH to LOW | [2] | - | 1.4 | - | μs |
| t _{s(poff)} | power-off settling time | P_i = -20 dBm; SHDN (pin 6) from LOW to HIGH | [2] | - | 0.4 | - | μs |
| K | Rollett stability factor | both on state and off state up to f = 20 GHz | | 1 | - | - | |
| $R_{\text{pd}(\text{SHDN})}$ | pull-down resistance on pin SHDN | | | - | 30 | _ | kΩ |

^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

Table 8. Shutdown control

 V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; R_{bias} = 5.1 k Ω ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 16 with components listed in Table 9 optimized for f = 2500 MHz

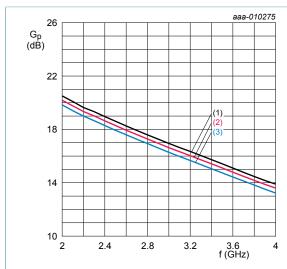
| State | V _{ctrl(sd)} [1] | Unit |
|-----------|---------------------------|------|
| on state | ≤ 0.6 | V |
| off state | ≥ 1.2 | V |

[1] Voltage on pin 6 (SHDN).

^[2] For TDD systems where fast switching is required, the value of C1 and C2 should be changed to 100 pF.

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11.1 Graphics



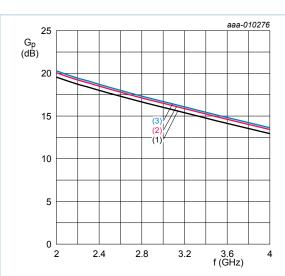
 $V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$

(1) $T_{amb} = -40^{\circ}C$

(2) $T_{amb} = +25^{\circ}C$

(3) $T_{amb} = +85^{\circ}C$

Figure 3. Power gain as a function of frequency; typical values



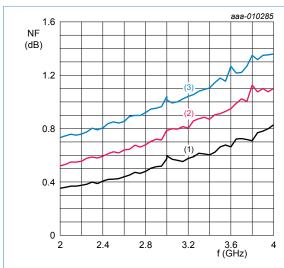
 $V_{CC} = 5 \text{ V}$; $T_{amb} = 25^{\circ}\text{C}$.

(1) $I_{CC} = 30 \text{ mA}$

(2) $I_{CC} = 45 \text{ mA}$

(3) $I_{CC} = 60 \text{ mA}$

Figure 4. Power gain as a function of frequency; typical values



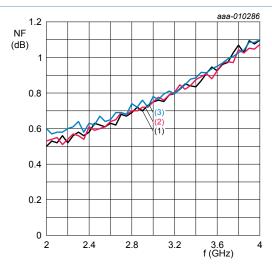
 $V_{CC} = 5 \text{ V;} I_{CC} = 48 \text{ mA}.$

(1) $T_{amb} = -40^{\circ}C$

(2) $T_{amb} = +25^{\circ}C$

(3) $T_{amb} = +85^{\circ}C$

Figure 5. Noise figure as a function of frequency; typical Figure 6. Noise figure as a function of frequency; typical



 V_{CC} = 5 V; T_{amb} = 25°C.

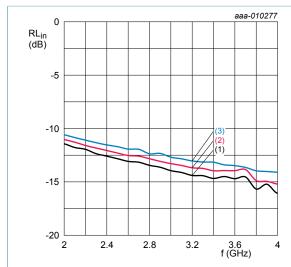
(1) $I_{CC} = 30 \text{ mA}$

(2) $I_{CC} = 45 \text{ mA}$

(3) $I_{CC} = 60 \text{ mA}$

values

Low noise high linearity amplifier



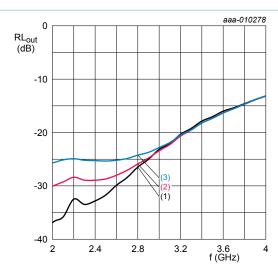
 V_{CC} = 5 V; I_{CC} = 48 mA.

(1)
$$T_{amb} = -40^{\circ}C$$

(2)
$$T_{amb} = +25^{\circ}C$$

(3)
$$T_{amb} = +85^{\circ}C$$

Figure 7. Input return loss as a function of frequency; typical values



 $V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$

(1)
$$T_{amb} = -40^{\circ}C$$

(2)
$$T_{amb} = +25^{\circ}C$$

(3)
$$T_{amb} = +85^{\circ}C$$

Figure 8. Output return loss as a function of frequency; typical values

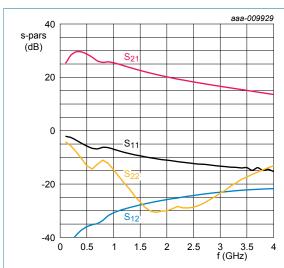
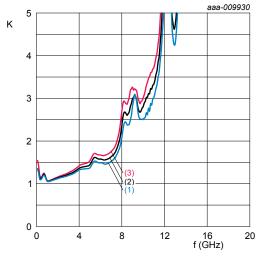


Figure 9. Wideband S-parameters as function of

 $V_{CC} = 5 \text{ V}; T_{amb} = 25^{\circ}\text{C}; I_{CC} = 48 \text{ mA}.$

frequency; typical values



 V_{CC} = 5 V; I_{CC} = 48 mA.

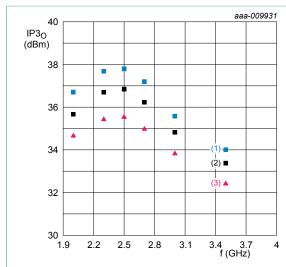
(1)
$$T_{amb} = -40^{\circ}C$$

(2)
$$T_{amb} = +25^{\circ}C$$

(3)
$$T_{amb} = +85^{\circ}C$$

Figure 10. Rollett stability factor as a function of frequency; typical values

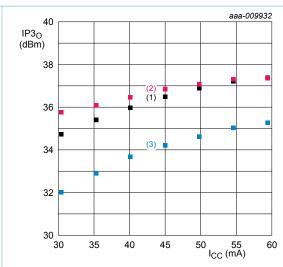
Low noise high linearity amplifier



 V_{CC} = 5 V; P_i = -15 dBm per tone; I_{CC} = 48 mA.

- (1) $T_{amb} = -40^{\circ}C$
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

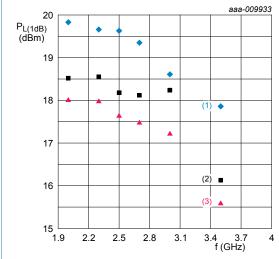
Figure 11. Output third-order intercept point as a function of frequency; typical values



 V_{CC} = 5 V; P_i = -15 dBm per tone; T_{amb} = 25°C.

- (1) f = 2000 MHz
- (2) f = 2500 MHz
- (3) f = 3000 MHz

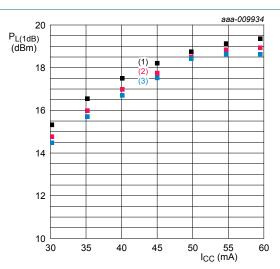
Figure 12. Output third-order intercept point as a function of supply current; typical values



 $V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$

- (1) $T_{amb} = -40^{\circ}C$
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

Figure 13. Output power at 1 dB gain compression as a function of frequency; typical values

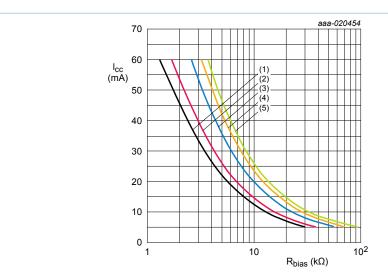


 V_{CC} = 5 V; T_{amb} = 25°C.

- (1) f = 2000 MHz
- (2) f = 2500 MHz
- (3) f = 3000 MHz

Figure 14. Output power at 1 dB gain compression as a function of supply current; typical values

Low noise high linearity amplifier



 $T_{amb} = 25^{\circ}C$

(1) $V_{CC} = 3.0 \text{ V}$

(2) $V_{CC} = 3.3 \text{ V}$ (3) $V_{CC} = 4.0 \text{ V}$

 $(4) V_{CC} = 4.5 V$

(5) $V_{CC} = 5 V$

Figure 15. I_{CC} as a function of R_{bias} , typical values

Low noise high linearity amplifier

12 Application information

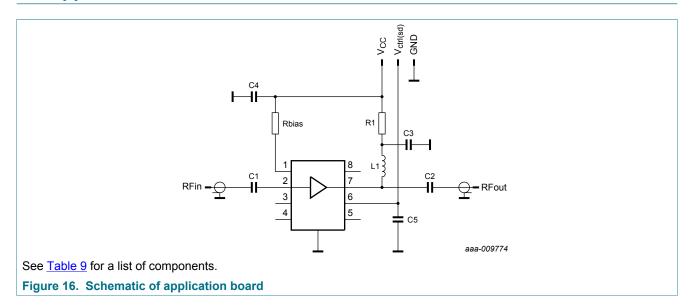


Table 9. List of components

See figure 16 for schematics.

| Component | Description | Value | Remarks |
|-------------------|-------------|--------|-----------------------------|
| C1, C2 | capacitor | 100 nF | |
| | | 100 pF | recommended for TDD systems |
| C3, C5 | capacitor | 10 pF | |
| C4 | capacitor | 10 nF | |
| L1 | inductor | 15 nH | |
| R1 | resistor | 10 Ω | |
| R _{bias} | resistor | 5.1 kΩ | V _{CC} = 5 V |
| | | 2.3 kΩ | V _{CC} = 3.3 V |

Low noise high linearity amplifier

Table 10. Typical performance BGU8053 application board V_{CC} = 5 V

All RF parameters are measured at the application board as shown in figure 16. With the components as listed in Table 9 while optimized for: f = 2500 MHz, V_{CC} = 5 V, I_{CC} = 48 mA and T_{amb} = 25 °C.

| Symbol | Parameter | Conditions | | f (MHz) | | | | | | | |
|---------------------|---------------------------------------|------------|------|---------|------|------|------|------|------|------|--|
| | | | 2000 | 2300 | 2500 | 2700 | 3000 | 3400 | 3500 | 3800 | |
| G | gain | | 20.2 | 19.0 | 18.3 | 17.6 | 16.6 | 15.4 | 15.1 | 14.2 | |
| RLin | input return loss | | 11.0 | 11.8 | 12.3 | 12.6 | 13.3 | 14.0 | 13.8 | 14.9 | |
| RL _{out} | output return loss | | 30.1 | 28.9 | 28.7 | 27.1 | 23.4 | 18.2 | 17.3 | 14.7 | |
| P _{L(1dB)} | output power at 1 dB gain compression | | 18.5 | 18.6 | 18.2 | 18.1 | 18.2 | 16.9 | 16.2 | 14.9 | |
| IP3 _O | output third-order | [1] | 35.5 | 35.4 | 35.4 | 35.2 | 34.3 | 33.4 | 33.3 | 32.5 | |
| intercept point | [1] [2] | 34.8 | 36.3 | 36.3 | 36.4 | 35.6 | 32.5 | 33.1 | 31.9 | | |
| NF | noise figure | [3] | 0.52 | 0.59 | 0.63 | 0.68 | 0.67 | 0.76 | 0.78 | 0.87 | |

Table 11. Typical performance BGU8053 application board V_{CC} = 3.3 V

All RF parameters measured at application board shown in figure 16. With the components as listed in Table 9 while optimized for 2500 MHz, V_{CC} = 3.3 V, I_{CC} = 48 mA, T_{amb} =25°C

| Symbol | Parameter | Conditions | | f (MHz) | | | | | | | |
|---------------------|---|------------|------|---------|------|------|------|------|------|------|--|
| | | | 2000 | 2300 | 2500 | 2700 | 3000 | 3400 | 3500 | 3800 | |
| G | gain | | 20.2 | 18.9 | 18.1 | 17.4 | 16.4 | 15.3 | 15.0 | 14.1 | |
| RLin | input return loss | | 11.3 | 12.1 | 12.4 | 14.1 | 13.6 | 13.7 | 15.0 | 15.3 | |
| RLout | output return loss | | 32.9 | 29.5 | 27.8 | 27.5 | 23.4 | 18.6 | 17.7 | 15.4 | |
| P _{L(1dB)} | output power at 1 dB gain compression | | 10.0 | 11.4 | 12.4 | 12.2 | 12.4 | 14.0 | 12.8 | 12.7 | |
| IP3 _O | output third-order | [1] | 30.5 | 30.3 | 28.8 | 29.3 | 27.8 | 29.5 | 27.9 | 26.1 | |
| | intercept point | [1] [2] | 31.0 | 30.7 | 28.8 | 29.3 | 27.4 | 29.4 | 27.6 | 26.0 | |
| NF | noise figure | [3] | 0.55 | 0.58 | 0.60 | 0.63 | 0.69 | 0.78 | 0.80 | 0.89 | |

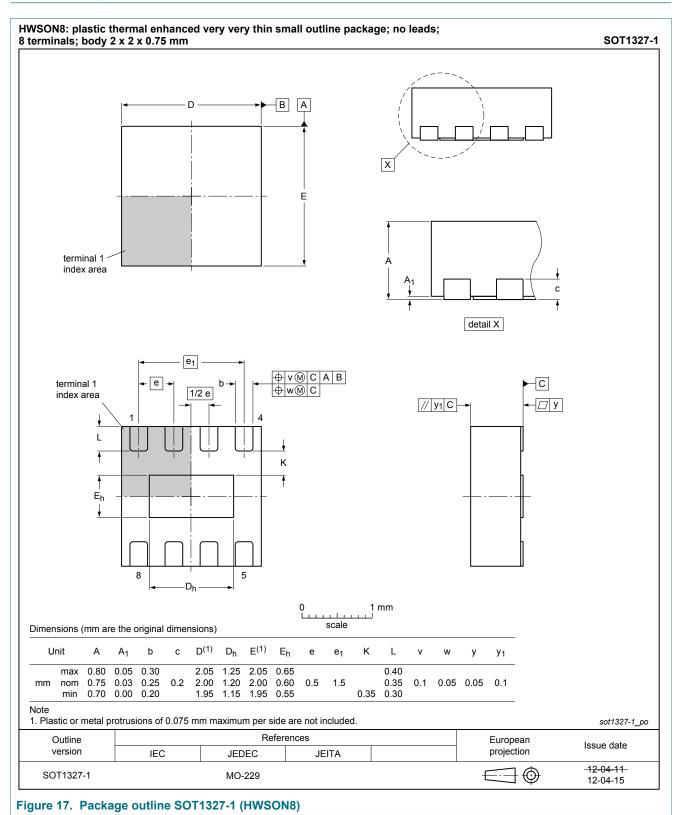
²⁻Tone; tone spacing = 1 MHz, P_0 = 5 dBm per tone. For TDD systems C1 and C2 have to be 100 pF.

²⁻Tone; tone spacing = 1 MHz, P_0 = 5 dBm per tone. For applications where fast switching is required, the value of C1 and C2 should be changed to 100 pF. Connector and board losses not de-embedded.

Connector and board losses not de-embedded.

Low noise high linearity amplifier

13 Package outline



Low noise high linearity amplifier

14 Abbreviations

Table 12. Abbreviations

| Acronym | Description |
|---------|--|
| CDMA | Code Division Multiple Access |
| ESD | ElectroStatic Discharge |
| FDD | Frequency-Division Duplexing |
| GSM | Global System for Mobile Communication |
| LNA | Low Noise Amplifier |
| LTE | Long-Term Evolution |
| RF | Radio Frequency |
| TDD | Time-Division Duplexing |
| W-CDMA | Wideband Code Division Multiple Access |

15 Revision history

Table 13. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|----------------|---|--------------------|---------------|-------------|--|
| BGU8053 v.7 | 201707017 | Product data sheet | - | BGU8053 v.6 | |
| Modifications: | <u>Section 11.1</u> has been changed | | | | |
| BGU8053 v.6 | 20170608 | Product data sheet | - | BGU8053 v.5 | |
| Modifications: | Table 4: the maximum value of V _{ESD} has been changed into 1.5 kV | | | | |
| BGU8053 v.5 | 20170502 | Product data sheet | - | BGU8053 v.4 | |
| Modifications: | <u>Table 5 "Recommended operating conditions"</u> : the minimum value of V _{CC} has been changed into 3.3 V | | | | |
| BGU8053 v.4 | 20170120 | Product data sheet | - | BGU8053 v.3 | |
| Modifications: | <u>Section 1 "General description"</u> : added BTS1001H according to our new naming convention | | | | |
| BGU8053 v.3 | 20160418 | Product data sheet | - | BGU8053 v.2 | |
| Modifications: | 3 V to 5 V single supply added to <u>Section 2 "Features and benefits"</u> Added <u>Figure 1 "Block diagram" on page 2</u> An additional curve added <u>Figure "Output power at 1 dB gain compression as a function of supply current; typical values" on page 8</u> Added remark to R_{bias} in <u>Table 9 "List of components"</u> Added <u>Table 11 "Typical performance BGU8053 application board VCC = 3.3 V" on page 11</u> | | | | |
| BGU8053 v.2 | 20131230 | Product data sheet | - | BGU8053 v.1 | |
| Modifications: | Table 4 on page 3: The maximum value for V _{ctrl(sd)} has been corrected to 3 V. | | | | |
| BGU8053 v.1 | 20131127 | Product data sheet | - | - | |

Low noise high linearity amplifier

16 Legal information

16.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions". [2] [3]
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Low noise high linearity amplifier

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BGU8053

Low noise high linearity amplifier

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